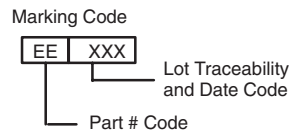
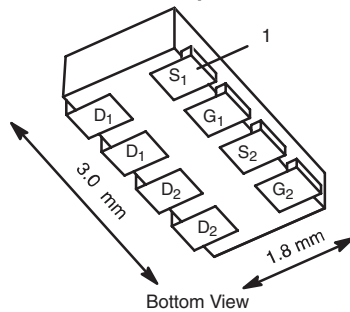


## N- and P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
	V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
N-Channel	30	0.055 at V <sub>GS</sub> = 4.5 V	4 <sup>a,g</sup>	4.2 nC
		0.090 at V <sub>GS</sub> = 2.5 V	4 <sup>a,g</sup>	
P-Channel	- 30	0.150 at V <sub>GS</sub> = - 4.5 V	- 3.6 <sup>a</sup>	2.85 nC
		0.256 at V <sub>GS</sub> = - 2.5 V	- 2.7 <sup>a</sup>	

1206-8 ChipFET®



### FEATURES

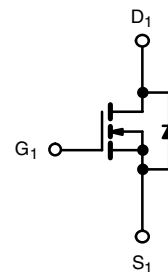
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



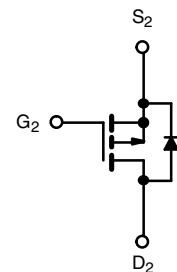
**RoHS**  
COMPLIANT  
**HALOGEN**  
**FREE**  
Available

### APPLICATIONS

- Buck-Boost
- DSC
- Portable Devices



N-Channel MOSFET



P-Channel MOSFET

Ordering Information: Si5511DC-T1-E3 (Lead (Pb)-free)  
Si5511DC-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	- 30	V
Gate-Source Voltage	V <sub>GS</sub>	± 12		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	4 <sup>a, g</sup>	- 3.6 <sup>a</sup>
		T <sub>C</sub> = 70 °C	4 <sup>a, g</sup>	- 2.8 <sup>a</sup>
		T <sub>A</sub> = 25 °C	4 <sup>a, g</sup>	- 2.3 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	3.9 <sup>a</sup>	- 1.8 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	15	- 10	A
Source Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	2.6	
		T <sub>A</sub> = 25 °C	1.7 <sup>b, c</sup>	- 1.7 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	3.1	2.6
		T <sub>C</sub> = 70 °C	2.0	1.7
		T <sub>A</sub> = 25 °C	2.1 <sup>b, c</sup>	1.3 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	1.33 <sup>b, c</sup>	0.84 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	50	60	77	95	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	30	40	33	40		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 110 °C/W for N-Channel and 130 °C/W for P-Channel.
- Package limited.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	30			V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-30			
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		24.2		mV/ $^\circ\text{C}$
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-23.1		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		3.6		
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		2.3		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.7		2	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.7		-2	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	N-Ch			100	nA
			P-Ch			-100	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			10	
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-10	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	N-Ch	15			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-10			
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 4.8\text{ A}$	N-Ch		0.045	0.055	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -2.3\text{ A}$	P-Ch		0.125	0.150	
		$V_{GS} = 2.5\text{ V}, I_D = 3.8\text{ A}$	N-Ch		0.075	0.090	
		$V_{GS} = -2.5\text{ V}, I_D = 1.8\text{ A}$	P-Ch		0.213	0.256	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 4.8\text{ A}$	N-Ch		10.8		S
		$V_{DS} = -15\text{ V}, I_D = -2.3\text{ A}$	P-Ch		6.56		
<b>Dynamic<sup>a</sup></b>							
Input Capacitance	$C_{iss}$	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$  P-Channel $V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		435		$\mu\text{F}$
			P-Ch		260		
Output Capacitance	$C_{oss}$		N-Ch		65		
			P-Ch		55		
Reverse Transfer Capacitance	$C_{rss}$		N-Ch		30		
			P-Ch		42		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 4.8\text{ A}$	N-Ch		4.7	7.1	nC
		$V_{DS} = -15\text{ V}, V_{GS} = -5\text{ V}, I_D = -3.2\text{ A}$	P-Ch		4.1	6.2	
		N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4.8\text{ A}$	N-Ch		4.2	6.3	
			P-Ch		3.8	4.6	
Gate-Source Charge	$Q_{gs}$	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -3.2\text{ A}$	N-Ch		1.1		
			P-Ch		0.6		
Gate-Drain Charge	$Q_{gd}$		N-Ch		0.9		
			P-Ch		1.85		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	N-Ch		2.7		$\Omega$
			P-Ch		7.7		

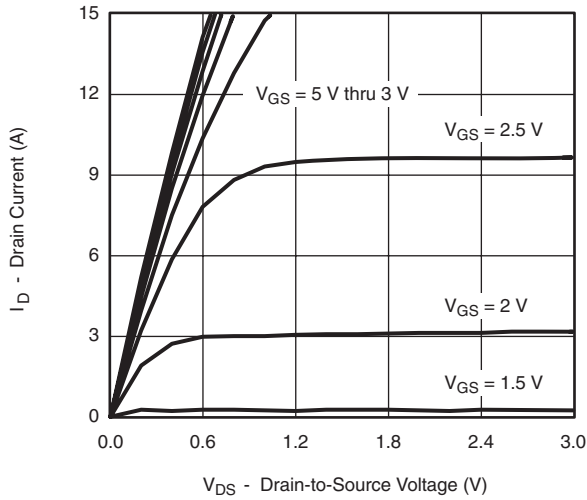
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit			
<b>Dynamic<sup>a</sup></b>									
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}$ , $R_L = 3.95\ \Omega$ $I_D \cong 3.8\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 1\ \Omega$	N-Ch		9	12	ns		
Rise Time	$t_r$		P-Ch		15	23			
Turn-Off Delay Time	$t_{d(off)}$	P-Channel $V_{DD} = -15\text{ V}$ , $R_L = 18.1\ \Omega$ $I_D \cong -1.86\text{ A}$ , $V_{GEN} = -4.5\text{ V}$ , $R_g = 1\ \Omega$	N-Ch		45	68			
			P-Ch		78	117			
Fall Time	$t_f$		N-Ch		48	72			
			P-Ch		33	50			
<b>Drain-Source Body Diode Characteristics</b>									
Continuous Source-Drain Diode Current	$I_S$		$T_C = 25\text{ }^\circ\text{C}$	N-Ch				2.6	A
				P-Ch			-2.6		
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$			N-Ch			15		
		P-Ch				-10			
Body Diode Voltage	$V_{SD}$	$I_S = 2.4\text{ A}$ , $V_{GS} = 0\text{ V}$ $I_S = -1.5\text{ A}$ , $V_{GS} = 0\text{ V}$	N-Ch		0.8	1.2	V		
			P-Ch		-0.8	-1.2			
Body Diode Reverse Recovery Time	$t_{rr}$	N-Channel $I_F = 2.4\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	N-Ch		11.6	18	ns		
Body Diode Reverse Recovery Charge	$Q_{rr}$		P-Ch		19.8	30			
Reverse Recovery Fall Time	$t_a$	P-Channel $I_F = -1.5\text{ A}$ , $di/dt = -100\text{ A}/\mu\text{s}$ , $T_J = 25\text{ }^\circ\text{C}$	N-Ch		6.1	9.2	nC		
			P-Ch		17.5	27			
Reverse Recovery Rise Time	$t_b$		N-Ch		8.4		ns		
			P-Ch		17.2				

Notes:

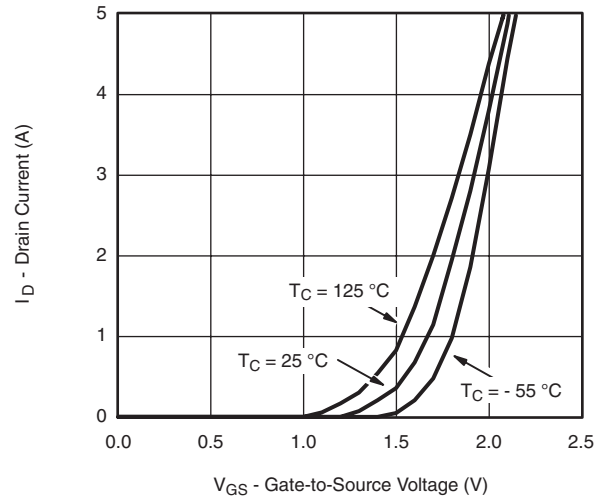
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

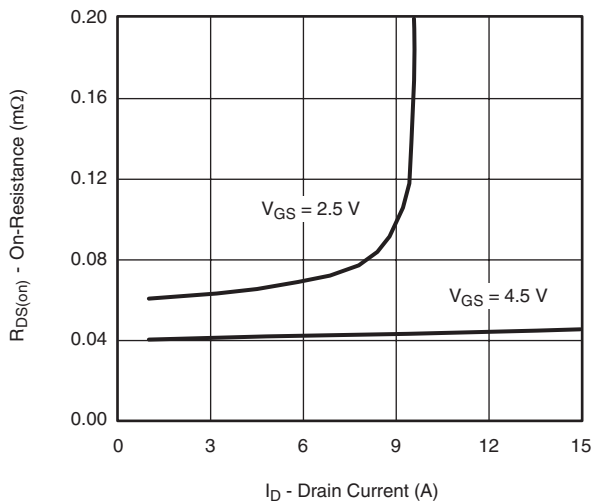
## N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



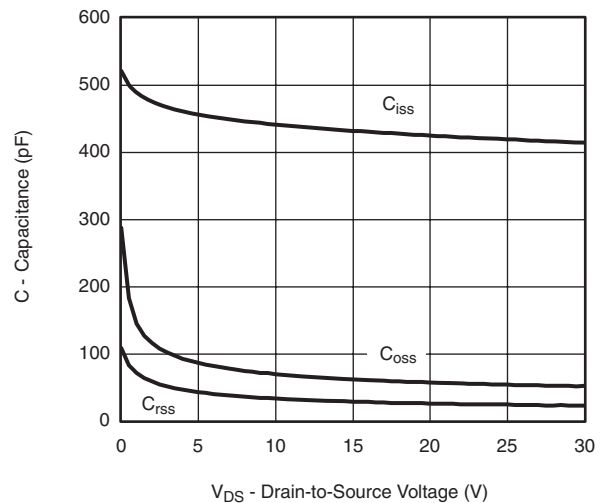
**Output Characteristics**



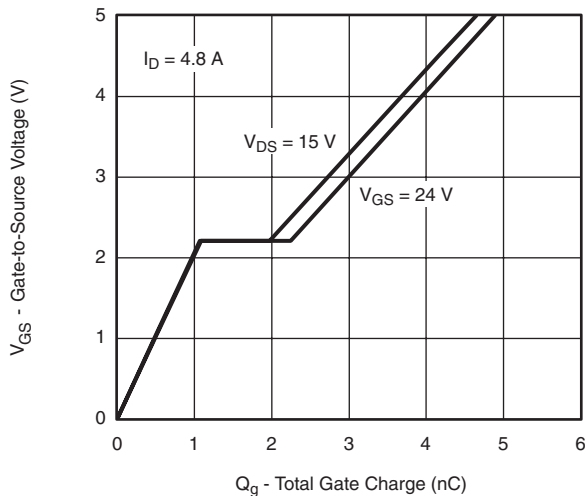
**Transfer Characteristics**



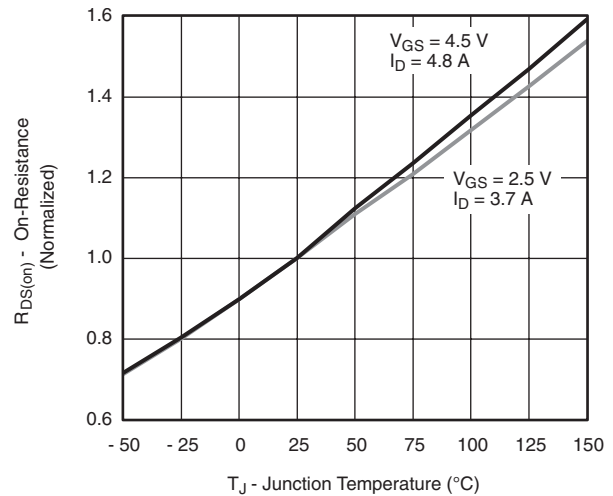
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

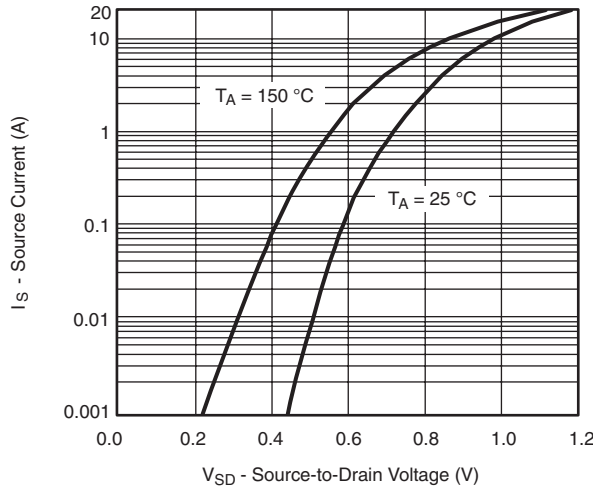


**Gate Charge**

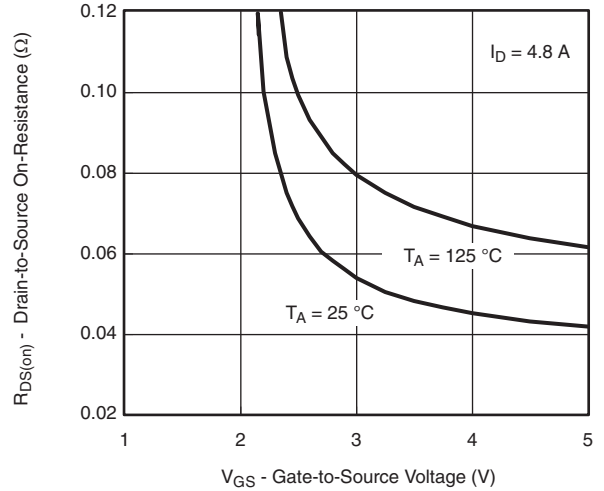


**On-Resistance vs. Junction Temperature**

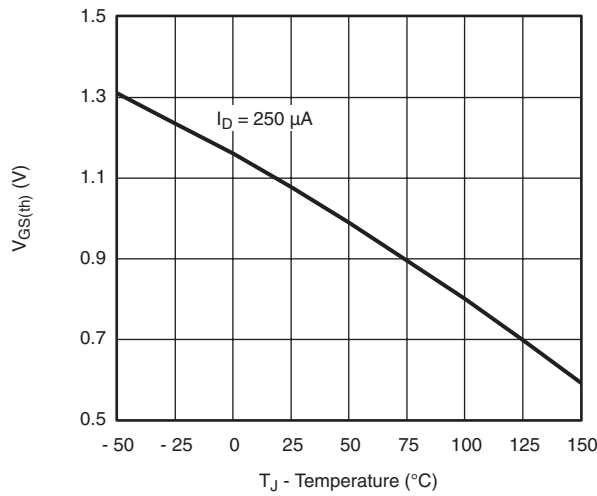
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



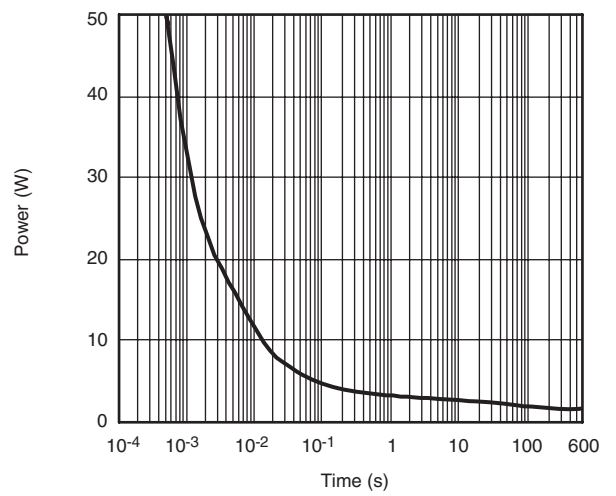
**Source-Drain Diode Forward Voltage**



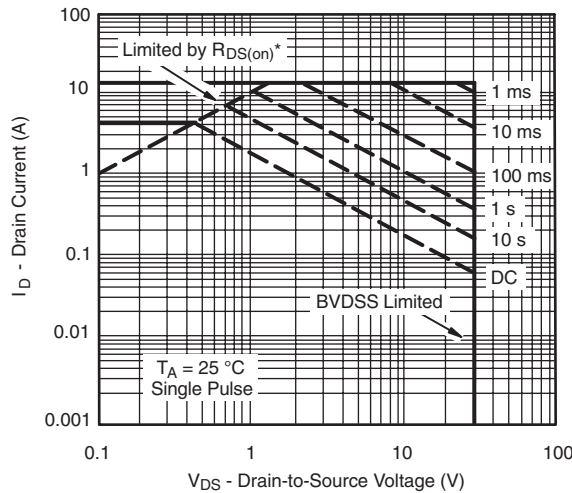
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



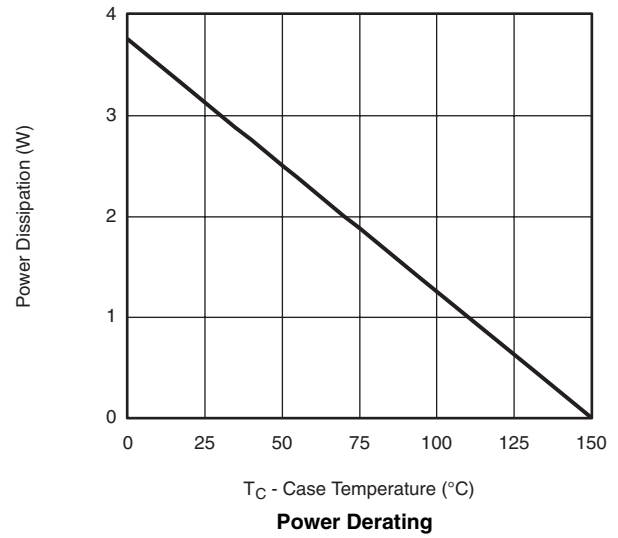
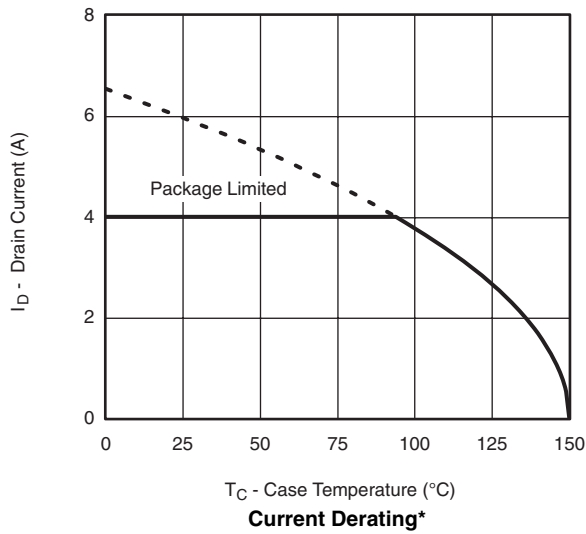
**Single Pulse Power**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

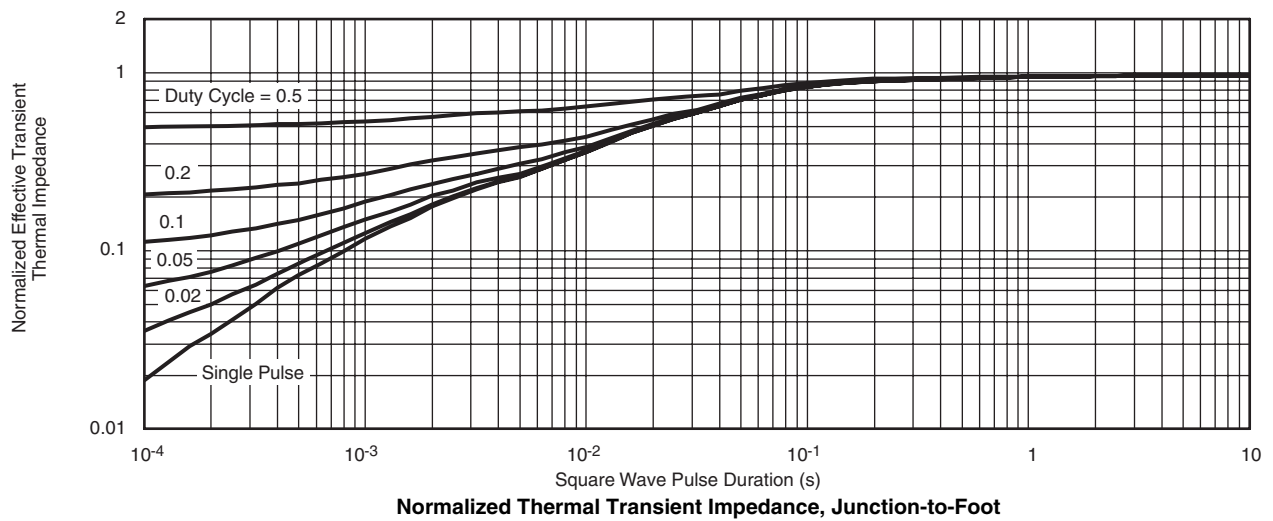
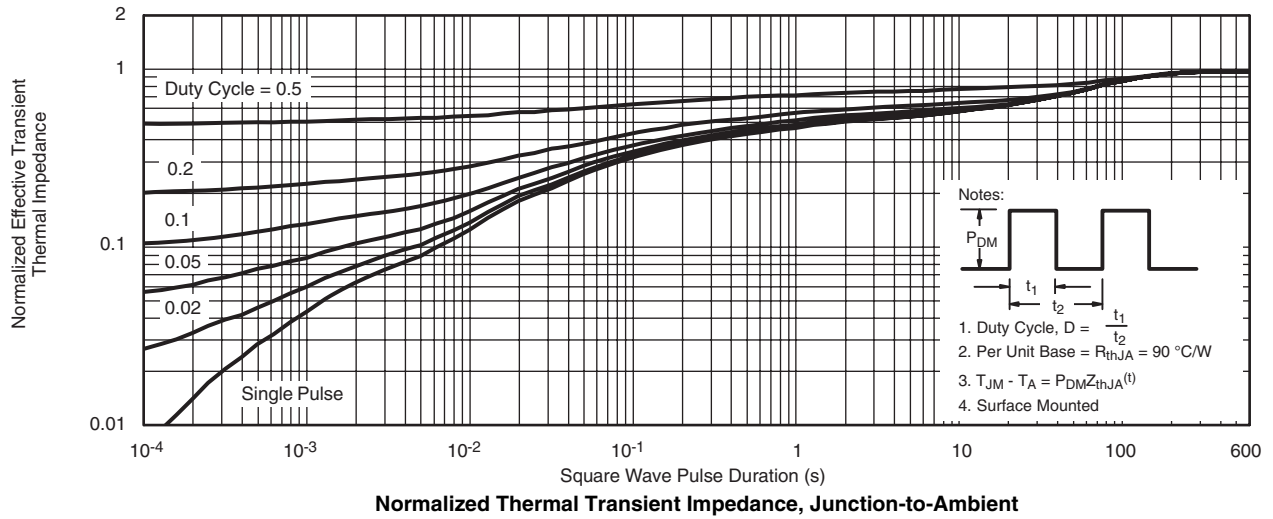
**Safe Operating Area, Junction-to-Ambient**

## N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

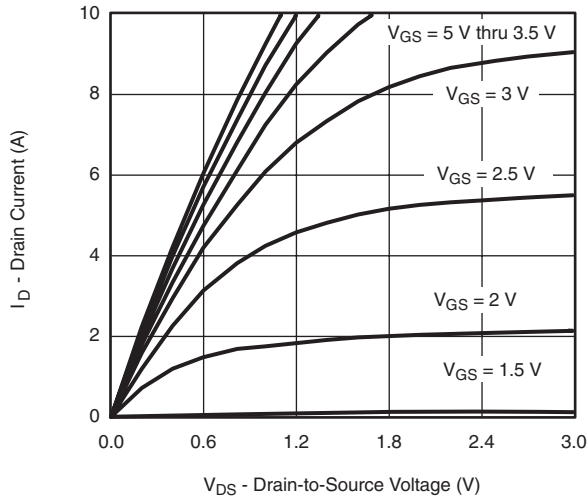


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

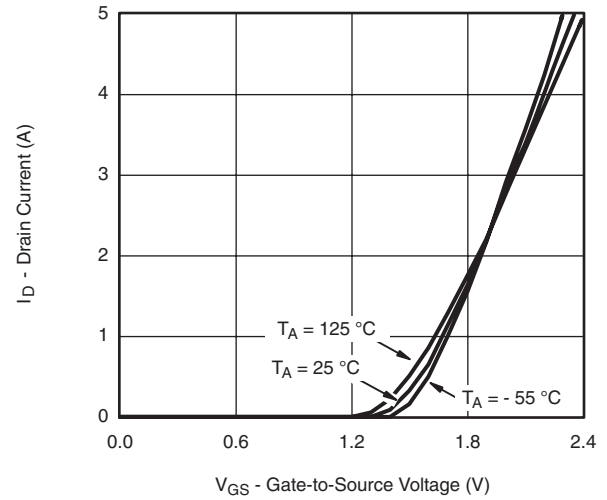
**N-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



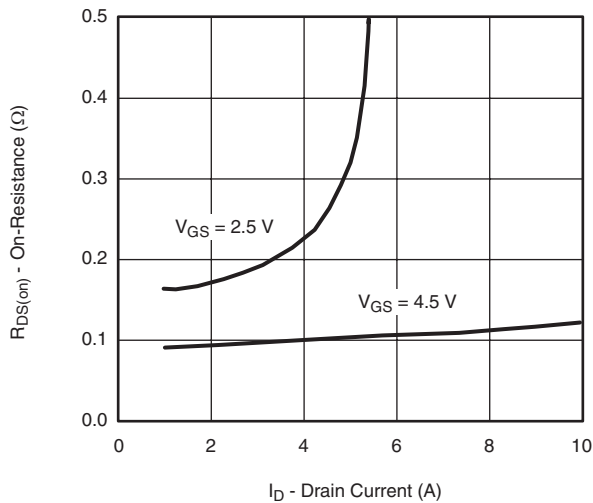
## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



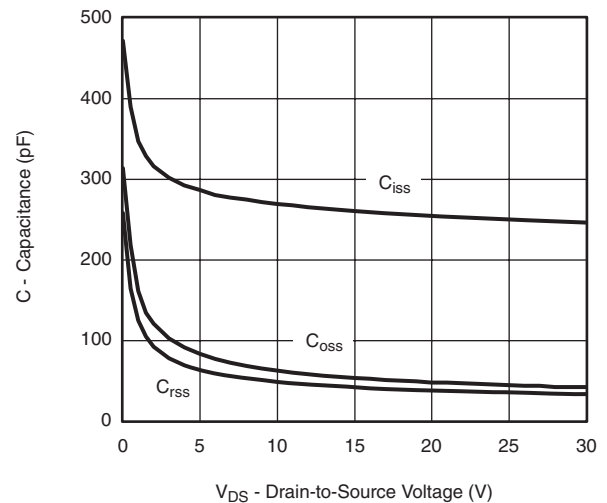
**Output Characteristics**



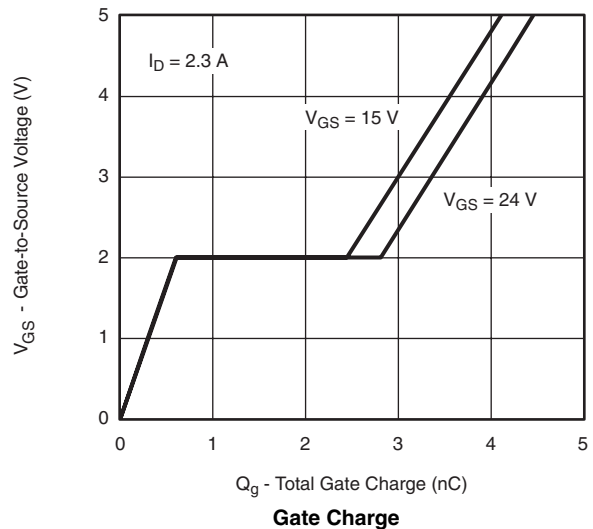
**Transfer Characteristics**



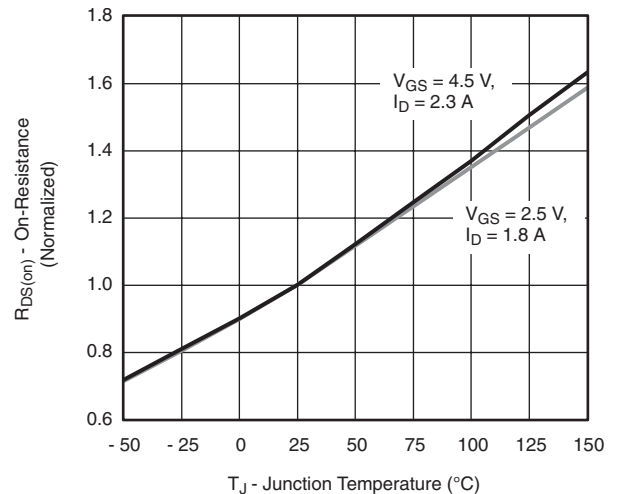
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



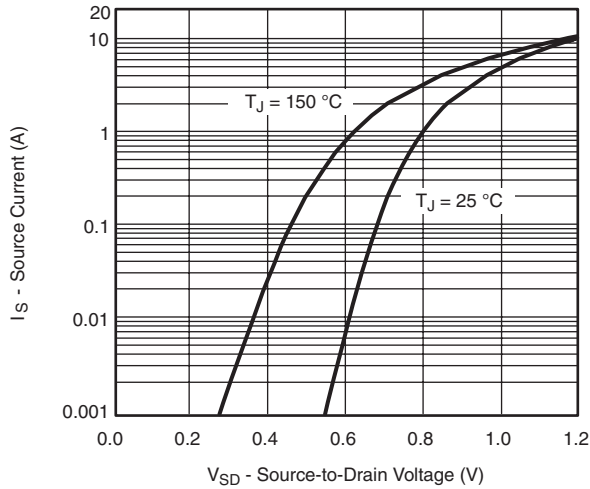
**Gate Charge**



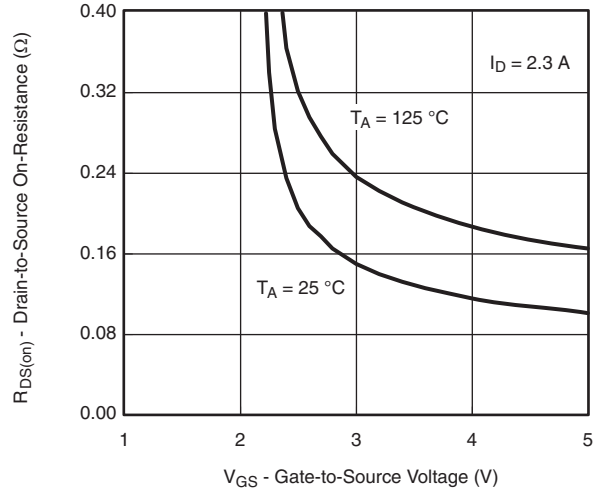
**On-Resistance vs. Junction Temperature**



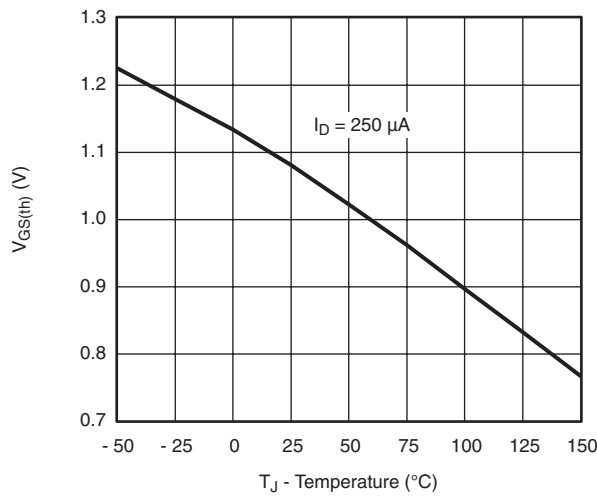
**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



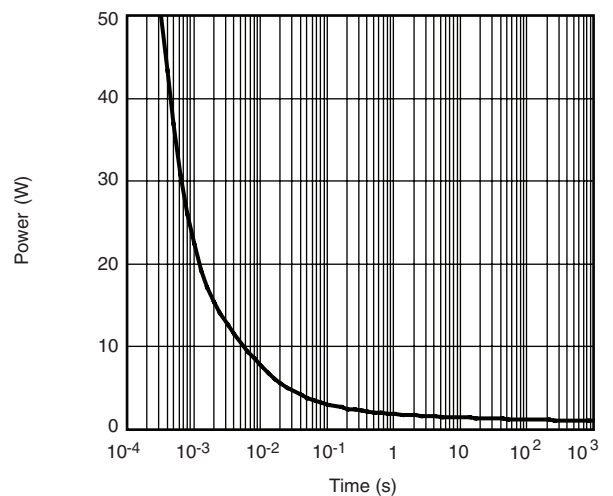
**Source-Drain Diode Forward Voltage**



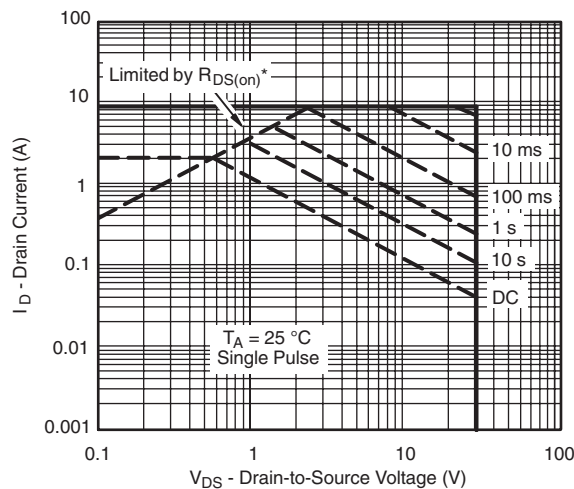
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



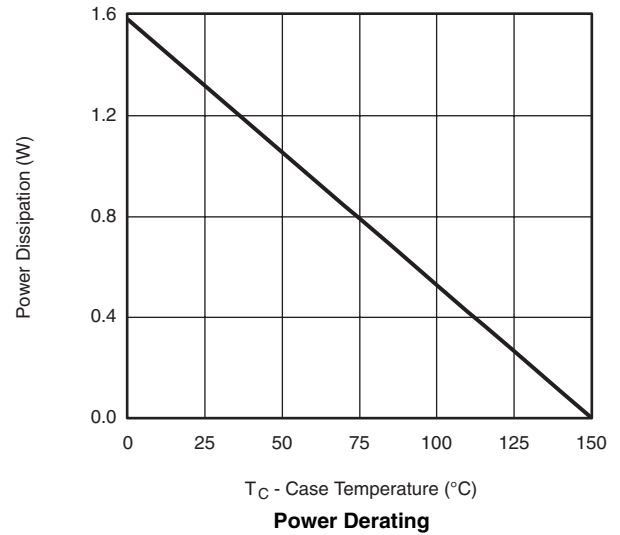
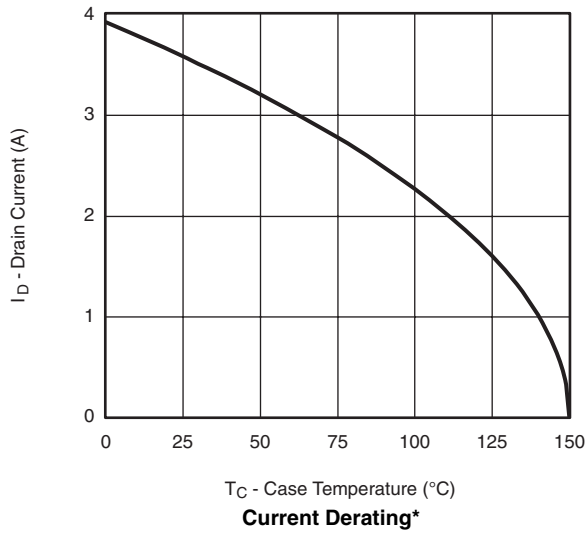
**Single Pulse Power**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

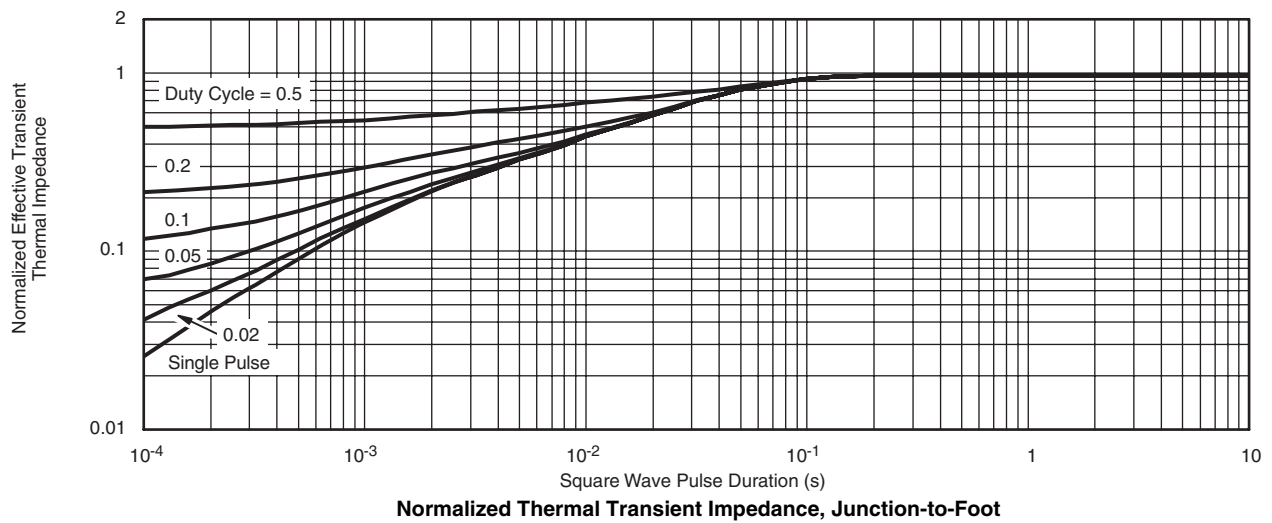
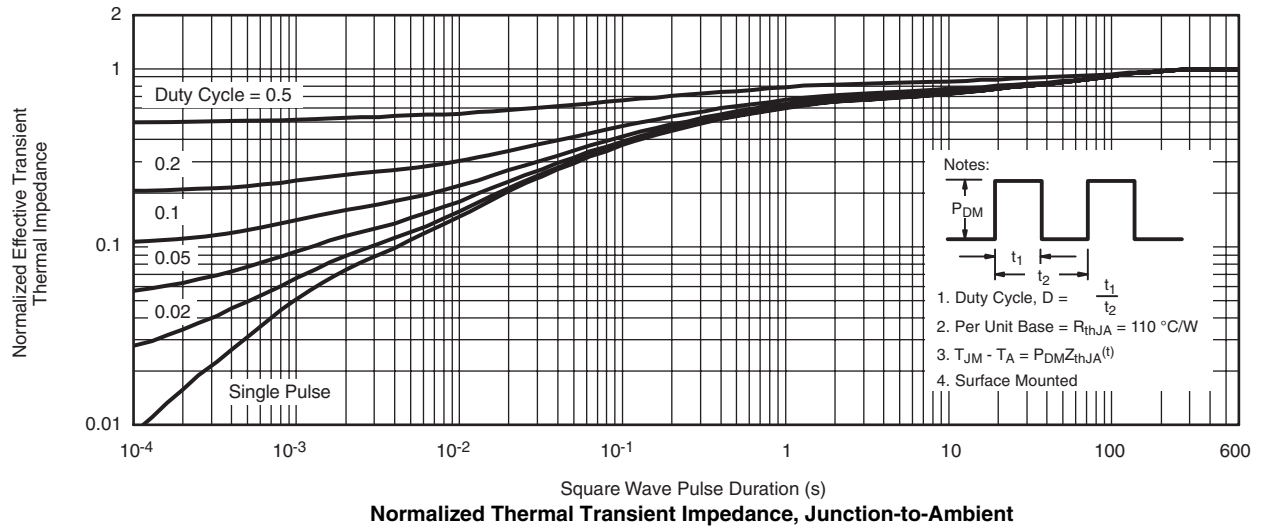
**Safe Operating Area, Junction-to-Case**

## P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**P-CHANNEL TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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